# 1.8V Drive Nch MOSFET RUF015N02

## Structure

Silicon N-channel MOSFET

## Features

- 1) Low On-resistance.
- 2) Space saving, small surface mount package (TUMT3).
- 3) Low voltage drive (1.8V drive).

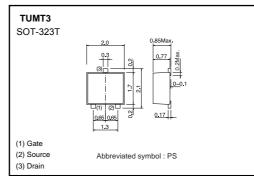
## Applications

Switching

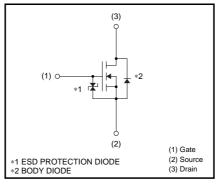
#### Packaging specifications

	Package	Taping	
Туре	Code	TL	
	Basic ordering unit (pieces)	3000	
RUF015N02		0	

## •Dimensions (Unit : mm)



#### Inner circuit



## •Absolute maximum ratings (Ta=25°C)

		<u> </u>		11.14
Parameter		Symbol	Limits	Unit
Drain-source voltage		Vdss	20	V
Gate-source voltage		Vgss	10	V
Drain current	Continuous	ID	±1.5	А
Drain current	Pulsed	I <sub>DP</sub> *1	±3.0	А
Source current	Continuous	ls	0.6	А
(Body diode)	Pulsed	I <sub>SP</sub> *1	2.4	А
Total power dissipation		P <sub>D</sub> *2	0.8	W
Channel temperature		Tch	150	°C
Range of storage temperature		Tstg	-55 to +150	°C
A Decision - Decisional a static				

\*1 Pw≤10µs, Duty cycle≤1%\*2 Mounted on a ceramic board

# Thermal resistance

Parameter	Symbol	Limits	Unit
Channel to ambient	Rth(ch-a)*	156	°C/W

\* Mounted on a ceramic board

# Transistors

## •Electrical characteristics (Ta=25°C)

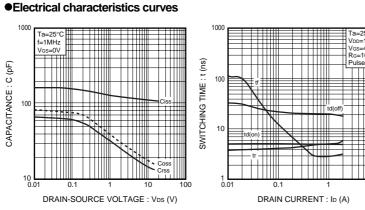
Parameter	Symbol	Min.	Тур.	Max.	Unit	Conditions
Gate-source leakage	Igss	-	-	10	μΑ	V <sub>GS</sub> =10V, V <sub>DS</sub> =0V
Drain-source breakdown voltage	V(BR) DSS	20	-	-	V	I <sub>D</sub> = 1mA, V <sub>GS</sub> =0V
Zero gate voltage drain current	IDSS	-	_	1	μΑ	V <sub>DS</sub> = 20V, V <sub>GS</sub> =0V
Gate threshold voltage	VGS (th)	0.3	-	1.0	V	V <sub>DS</sub> = 10V, I <sub>D</sub> = 1mA
Static drain-source on-state resistance		-	130	180	mΩ	ID= 1.5A, VGs= 4.5V
	RDS (on)*	-	170	240	mΩ	I <sub>D</sub> = 1.5A, V <sub>GS</sub> = 2.5V
		-	220	310	mΩ	I <sub>D</sub> = 0.8A, V <sub>GS</sub> = 1.8V
Forward transfer admittance	Y <sub>fs</sub> *	1.6	-	-	S	V <sub>DS</sub> = 10V, I <sub>D</sub> = 1.5A
Input capacitance	Ciss	-	110	-	pF	VDS= 10V
Output capacitance	Coss	-	18	-	рF	V <sub>GS</sub> =0V
Reverse transfer capacitance	Crss	-	15	-	pF	f=1MHz
Turn-on delay time	td (on) *	-	5	_	ns	ID= 1.0A
Rise time	tr *	-	5	-	ns	$V_{DD} = 10V$
Turn-off delay time	td (off) *	-	20	-	ns	VGs= 4.5V R∟=10Ω
Fall time	t <sub>f</sub> *	-	3	-	ns	Rg=10Ω
Total gate charge	Qg *	-	1.8	2.5	nC	V <sub>DD</sub> ≒10V
Gate-source charge	Qgs *	-	0.3	-	nC	Vgs= 4.5V
Gate-drain charge	Q <sub>gd</sub> *	-	0.3	-	nC	I <sub>D</sub> = 1.5A

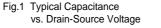
## •Body diode characteristics (Source-drain) (Ta=25°C)

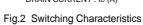
Parameter	Symbol	Min.	Тур.	Max.	Unit	Conditions
Forward voltage	Vsd	-	-	1.2	V	Is= 0.6A, V <sub>GS</sub> =0V

# Transistors

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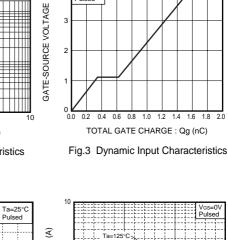






=1.5A

2 3 4



75%

Ta=25°C VDD=10V ID=1.5A RG=10Ω

Pulsed

VGS (V)

4

3

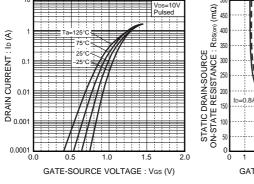
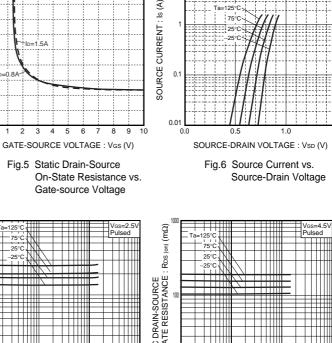
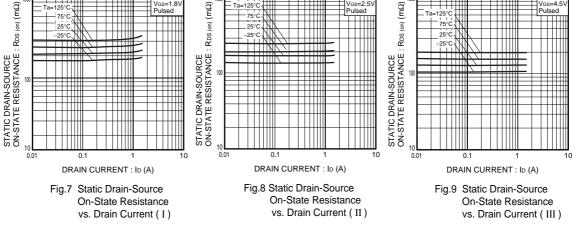


Fig.4 Typical Transfer Characteristics

Fig.5 Static Drain-Source On-State Resistance vs.





## Notice

This product might cause chip aging and breakdown under the large electrified environment. Please consider to design ESD protection circuit.

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Appendix1-Rev2.0

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